# UNR7231 (UN7231)

## Silicon NPN epitaxial planar type

For low-frequency amplification

#### Features

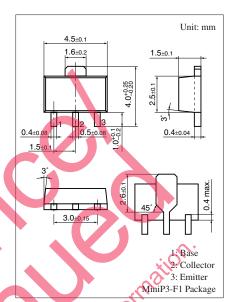
• High forward current transfer ratio h<sub>FE</sub>

Absolute Maximum Ratings  $T = 25^{\circ}C$ 

• Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

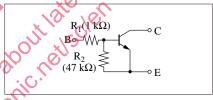
Absolute maximum matings $T_a = 25$ C							
Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	20	V				
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V				
Collector current	I <sub>C</sub>	0.7	A				
Peak collector current	I <sub>CP</sub>	1.5	A				
Total power dissipation *	P <sub>T</sub>	1.0	W				
Junction temperature	Tj	150	°C				
Storage temperature	T <sub>stg</sub>	-55 to +150	°C				

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion



Marking Symbol: IC

#### Internal Connection



## Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

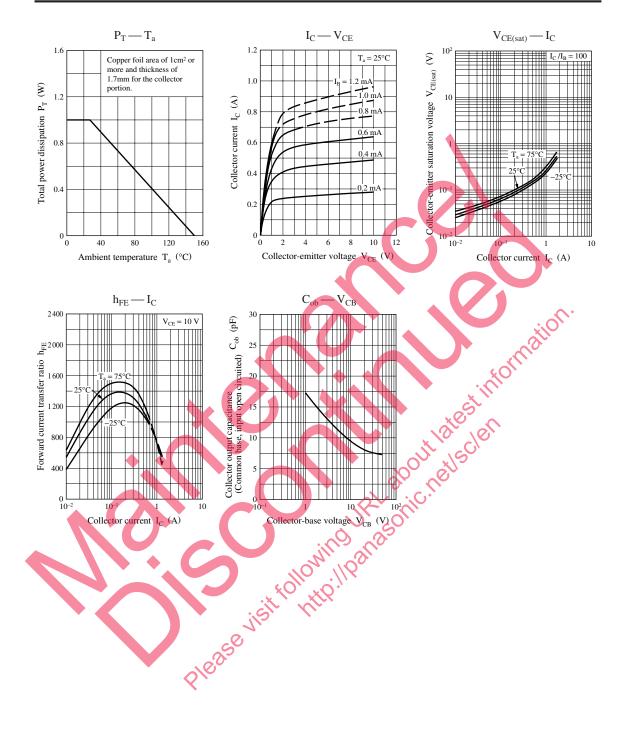
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	20			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1$ mA, $I_{\rm B} = 0$	20			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 15 V, I_E = 0$			1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 15 V, I_B = 0$			10	μΑ
Emitter-base cutoff current (Collector open)	IEBO	$V_{EB} = 14 \text{ V}, I_C = 0$			0.5	mA
Forward current transfer ratio *	hre	$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$	800		2100	—
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{C} = 500 \text{ mA}, I_{B} = 5 \text{ mA}$			0.4	V
Input resistance	R <sub>1</sub>		0.7	1.0	1.3	kΩ
Resistance ratio	R <sub>1</sub> /R <sub>2</sub>		0.016	0.021	0.025	
Transition frequency	f <sub>T</sub>	$V_{CB} = 20 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$		55		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Pulse measurement

Note) The part number in the parenthesis shows conventional part number.

# Panasonic



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